Micro Commercial Components
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MPSA94

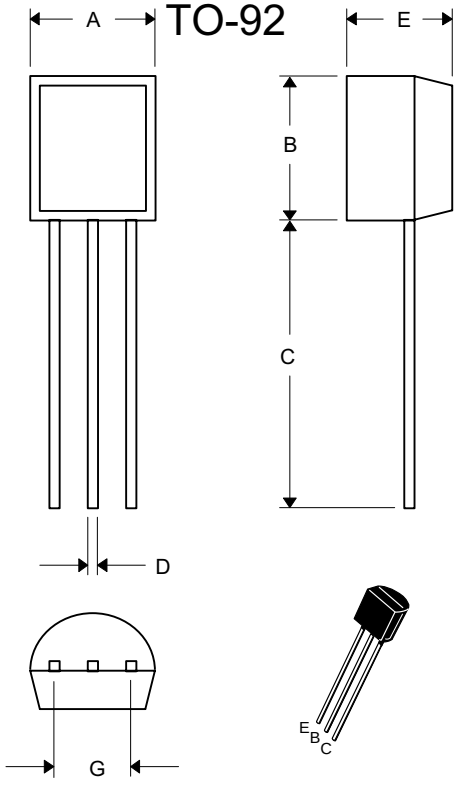
PNP Silicon High Voltage Transistor 625mW

Features

- Through Hole Package
- 150°C Junction Temperature
- Epoxy meets UL 94 V-0 flammability rating
- Moisure Sensitivity Level 1
- Lead Free Finish/RoHS Compliant ("P" Suffix designates RoHS Compliant. See ordering information)

Mechanical Data

- Case: TO-92, Molded Plastic
- Marking:A94



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
A	.170	.190	4.33	4.83	
B	.170	.190	4.30	4.83	
C	.550	.590	13.97	14.97	
D	.010	.020	0.36	0.56	
E	.130	.160	3.30	3.96	
G	.096	.104	2.44	2.64	

Maximum Ratings @ 25°C Unless Otherwise Specified

Charateristic	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-400	V
Collector-Base Voltage	V_{CBO}	-400	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current(DC)	I_C	-200	mA
Power Dissipation@T_A=25°C	P_d	625 5.0	mW mW/°C
Power Dissipation@T_C=25°C	P_d	1.5 12	W mW/°C
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Operating & Storage Temperature	T_j, T_{STG}	-55~150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage(1) (I_C = -1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	-400	—	Vdc
Collector–Base Breakdown Voltage (I_C = -100 ı uAdc Ł I_E = 0)	$V_{(BR)CBO}$	-400	—	Vdc
Emitter–Base Breakdown Voltage (I_E = -100uAdc, I_C = 0)	$V_{(BR)EBO}$	-5.0	—	Vdc
Collector Cutoff Current (V_{CB} = -300 Vdc, I_E = 0)	I_{CBO}	—	-0.1	µAdc
Emitter Cutoff Current (V_{EB} = -4.0 Vdc, I_C = 0)	I_{EBO}	—	-0.1	µAdc
ON CHARACTERISTICS(1)				
DC Current Gain(1) (I_C = -1.0 mAdc, V_{CE} = -10 Vdc) (I_C = -10 mAdc, V_{CE} = -10 Vdc) (I_C = -100 mAdc, V_{CE} = -10 Vdc)	h_{FE}	 70 80 60	 300	
Collector–Emitter Saturation Voltage(1) (I_C = -10 mAdc, I_B = -1.0 mAdc) (I_C = -50 mAdc, I_B = -5.0 mAdc)	$V_{CE(sat)}$	 — —	 -0.2 -0.3	Vdc
Base–Emitter Saturation Voltage (I_C = -10 mAdc, I_B = -1.0 mAdc)	$V_{BE(sat)}$	—	-0.75	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	7.0	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	—	130	pF
Small–Signal Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)	h_{fe}	1.0	—	—

1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

Ordering Information :

Device	Packing
Part Number-AP	Ammo Packing: 2Kpcs/Ammo Box
Part Number-BP	Bulk: 100Kpcs/Carton